# Effects of $ZrO_2$ and $Y_2O_3$ dissolved in zyttrite on the densification and the $\alpha/\beta$ phase transformation of $Si_3N_4$ in $Si_3N_4$ –ZrO<sub>2</sub> composite

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In Si<sub>3</sub>N<sub>4</sub>–ZrO<sub>2</sub> composite, the effects of zirconia and Y<sub>2</sub>O<sub>3</sub> dissolved in zyttrite on the densification and the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> were studied using hot-pressing of Si<sub>3</sub>N<sub>4</sub> with the addition of pure, 3, 6, and 8 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia. Reaction couples between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub> of zyttrite were made to observe the reaction phenomena. The addition of pure zirconia was not effective to obtain full density of the Si<sub>3</sub>N<sub>4</sub>–ZrO<sub>2</sub> composite. However, Y<sub>2</sub>O<sub>3</sub> diffused from the added zyttrite promoted densification; the density of Si<sub>3</sub>N<sub>4</sub> with 5 vol % pure ZrO<sub>2</sub> composite was 71% theoretical, and nearly full density (>97%) could be obtained in Si<sub>3</sub>N<sub>4</sub> with 5 vol % 6, 8 mol% Y<sub>2</sub>O<sub>3</sub>-doped ZrO<sub>2</sub> composite. On the basis of observations of the Si<sub>3</sub>N<sub>4</sub>-pure ZrO<sub>2</sub> reaction couple, the reaction between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub> resulted in the formation of Si<sub>2</sub>N<sub>2</sub>O phase, and the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> and zrO<sub>2</sub> resulted that the reaction products, Y<sub>2</sub>Si<sub>2</sub>O<sub>7</sub> and Y<sub>2</sub>Si<sub>3</sub>N<sub>4</sub>O<sub>3</sub> phases, play an important role in the densification of Si<sub>3</sub>N<sub>4</sub> –zyttrite composite.

#### 1. Introduction

Silicon nitride is a well-known candidate material for heat engine and cutting tools, because of its good thermal-shock resistance, high-temperature strength and oxidation resistance. Generally, a dense silicon nitride body is fabricated by pressureless sintering, hot-pressing or hot isostatic pressing processes with the addition of sintering aids, such as MgO, Y<sub>2</sub>O<sub>3</sub>, CeO<sub>2</sub>, etc. Since 1975, a few workers have studied hot-pressed Si<sub>3</sub>N<sub>4</sub> with the addition of mono-zirconia or zyttrite (yttria-stabilized zirconia) [1-9]. These  $Si_3N_4$ -ZrO<sub>2</sub> composites were shown to be superior to hot-pressed  $Si_3 N_4$  with MgO with regard to room- and high-temperature strength, oxidation resistance and capability as cutting tools [6–8]. Lange [4] reported that toughness could be increased by compressive surface stress resulting from the oxidation of  $Si_3N_4$ -ZrO<sub>2</sub> composite.

Previously, workers were primarily concerned about the effects of added zirconia on the beneficial properties of Si<sub>3</sub>N<sub>4</sub> ceramics, thus little is known about the details of the effects of zirconia on the densification and the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> [4–10]. Moreover, the behaviour of Y<sub>2</sub>O<sub>3</sub> dissolved in zyttrite has been almost neglected in Si<sub>3</sub>N<sub>4</sub>–zyttrite composite.

In the present work, the effects of  $ZrO_2$  and  $Y_2O_3$ dissolved in zyttrite on the densification and the  $\alpha/\beta$ phase transformation of Si<sub>3</sub>N<sub>4</sub> were studied using pure 3, 6, and 8 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia powder without any other sintering aids. In order to observe the reaction phenomena between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub> (pure or zyttrite), reaction couples were made. Specimens for this study were made by hot-pressing.

#### 2. Experimental procedure

Commercially available Si<sub>3</sub>N<sub>4</sub> powder (LC-12, H. C. Starck, Berlin, West Germany; ratio of  $\alpha$  and  $\beta$  is 94 to 3 and contained less than 0.1 wt % free silicon) and 0, 3, 6, 8 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia (TZ-0 and TZ-3Y, 6Y, 8Y, respectively, Toyo Soda Co., Tokyo, Japan; for convenience, Y<sub>2</sub>O<sub>3</sub>-doped zirconia powders are expressed as a zyttrite in this article) (denoted 0Y, 3Y, 6Y, and 8Y, respectively) powders were used to prepare the mixtures of  $Si_3N_4$  and 5, 10, 15, 20, and 30 vol % of various zirconia. The mixtures were centrifugally mixed in acetone for 2 h using zirconia balls and jar (Pulverisette 6, Fritsch, West Germany). For more uniform mixing of  $Si_3N_4$  and zirconia powders, these mixtures were again vibration mixed (Spex 8000 mixer/mill, Edison, New Jersey, USA) for 10 min in a teflon-coated container with zirconia balls, and then dried in an oven.

The dried mixture screened to -60 mesh, was hotpressed in a tungsten mesh heater furnace (Model 60 series, Centorr Associate, Inc., Suncook, New Hampshire, USA) using BN coated graphite die (2 cm i.d.). 1 atm N<sub>2</sub> atmosphere was maintained during hotpressing, and the temperature and pressure were 1750°C and 35 MN m<sup>-2</sup>, respectively. Temperature was measured pyrometrically to  $\pm$  5°C.

For the reaction couples between  $Si_3N_4$  and pure  $ZrO_2(0Y)$  or zyttrite, as-received  $Si_3N_4$  powder was



Figure 1 Schematic diagram of Si<sub>3</sub>N<sub>4</sub>-ZrO<sub>2</sub> reaction couple.

die-pressed to form discs (1 cm i.d.) and subsequently cold isostatically pressed at  $150 \text{ MN m}^{-2}$ . These compacts were, then embedded in 0Y, 3Y and 8Y zirconia powder as shown in Fig. 1. These reaction couples were hot-pressed under the same conditions described above.

Microstructural characterization of the interface of reaction couples, was made by optical microscopy (Zeiss, West Germany) and scanning electron microscopy (SEM, ETEC Autoscan Co., Hayward, California, USA), and phase identification was performed by X-ray diffraction (XRD, Rigaku, Japan). Transmission electron microscopy (TEM, Model 200 CX, Jeol, Tokyo, Japan) was used to distinguish cubic and tetragonal zirconia phase in Si<sub>3</sub>N<sub>4</sub> matrix. The electron transparent specimen for TEM was obtained by argon-ion bombardment technique (MIN, Technics, Inc., USA). The specimen was thinned from both sides with an incident angle of 15° with an average voltage of 5kV. The density of the hot-pressed body was determined by Archimedes method, and the theoretical density was calculated by the rule of mixture.

#### 3. Results and discussion

#### 3.1. Si<sub>3</sub>N<sub>4</sub>-ZrO<sub>2</sub> composites

# 3.1.1. Effect of added zirconia on the densification

Pure  $Si_3N_4$  and the mixtures of  $Si_3N_4$  and 5 vol % 0Y, 3Y, 6Y, and 8Y ZrO<sub>2</sub> were hot-pressed to investigate





Figure 2 Variations of relative density of hot-pressed  $Si_3N_4$  with 5 vol % ZrO<sub>2</sub> composite with the addition of various zirconia (pure, 3, 6, 8 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia) and hot-pressed pure  $Si_3N_4$ .



*Figure 3* Variations of relative density of hot-pressed  $Si_3N_4$  with (O) 3, ( $\Box$ ) 6, ( $\Delta$ ) 8 mol %  $Y_2O_3$ -doped zirconia composite with the amount of added zirconia.

the effect of zirconia on the densification. Fig. 2 shows the final densities obtained by hot-pressing pure  $Si_3N_4$ , mixtures of  $Si_3N_4$  and various zirconia. The addition of only 5 vol % 6Y and 8Y zirconia increased the density up to 97% and 99% theoretical, respectively. However, the density of pure  $Si_3N_4$  was low (57%). Therefore, densification did not take place in hot-pressed pure  $Si_3N_4$ . The density of  $Si_3N_4$  with 5 vol % 0Y ZrO<sub>2</sub> composite (71%) was higher than that of pure  $Si_3N_4$ . From these results,  $Y_2O_3$  in zyttrite affected the densification dominantly rather than  $ZrO_2$ phase.

Fig. 3 shows the variations in density of hot-pressed Si<sub>3</sub>N<sub>4</sub>-zyttrite composite with the amount of added 3Y, 6Y, 8Y zirconia. Si<sub>3</sub>N<sub>4</sub> with 6Y and 8Y zirconia composites show high densities (97%) regardless of the amount of added zirconia, but densities of  $Si_3N_4$ with 3Y ZrO<sub>2</sub> composite cannot exceed 80% theoretical up to 20 vol % zirconia. These results support the fact that densification of these composites is mainly affected by the content of Y<sub>2</sub>O<sub>3</sub> in zyttrite. According to Fick's first law, the total amount of Y<sub>2</sub>O<sub>3</sub> diffused from zyttrite depends on the  $\Delta C$  (concentration gradient of  $Y_2O_3$  between zyttrite and the matrix) and temperature. Therefore, significant densification could not occur when 3Y ZrO<sub>2</sub> was added to Si<sub>3</sub>N<sub>4</sub>, because  $\Delta C$ of 3Y ZrO<sub>2</sub> was lower than that of 6Y and 8Y ZrO<sub>2</sub>. Moreover, nearly full density (98%) was obtained in  $Si_3N_4$  with 5 vol % 3Y ZrO<sub>2</sub> composite by raising the hot-pressing temperature up to 1850° C i.e. increasing D: diffusivity, D, is exponentially proportional to the temperature. So, it is concluded that  $Y_2O_3$  diffused from zyttrite promotes the densification of  $Si_3N_4$ zyttrite composite. But the  $Si_3N_4$  and zyttrite system involves various chemical reaction processes; the diffusion process is not simply expressed as described above. Thus, to explain fully the density variations with the addition of  $3Y ZrO_2$ , further work is required to complement the diffusion process.

#### 3.1.2. Phase identification

In order to evaluate the role of the zirconia on the  $\alpha/\beta$ 



*Figure 4* XRD pattern of (a) as-received Si<sub>3</sub>N<sub>4</sub> powder, (b) hot-pressed pure Si<sub>3</sub>N<sub>4</sub>, (c) hot-pressed Si<sub>3</sub>N<sub>4</sub> with 5 vol % 3 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia composite, and (d) hot-pressed Si<sub>3</sub>N<sub>4</sub> with 5 vol % 6 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia composite: (A)  $\alpha$ -Si<sub>3</sub>N<sub>4</sub>, (B)  $\beta$ -Si<sub>3</sub>N<sub>4</sub>, (O) Si<sub>2</sub>N<sub>2</sub>O, (Z) cubic or tertragonal zirconia, (M) monoclinic zirconia peaks.

phase transformation of Si<sub>3</sub>N<sub>4</sub>, X-ray analysis was performed (Fig. 4). A significant  $\alpha/\beta$  ratio change could not be detected in hot-pressed pure Si<sub>3</sub>N<sub>4</sub> composite\* compared to the starting powder (0.044), Figs 4a, b. However in Si<sub>3</sub>N<sub>4</sub>-0Y ZrO<sub>2</sub> composite,  $\beta$ -Si<sub>3</sub>N<sub>4</sub> and Si<sub>2</sub>N<sub>2</sub>O (silicon oxynitride) peaks were detected together (Fig. 4c). Therefore, ZrO<sub>2</sub> phase seems to be concerned with the formation of Si<sub>2</sub>N<sub>2</sub>O phase, and the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> also seems to be caused by this Si<sub>2</sub>N<sub>2</sub>O phase; this will be discussed in detail in a later section. With this, it is conceivable that the density of Si<sub>3</sub>N<sub>4</sub> with 0Y ZrO<sub>2</sub> composite, compared with that of the hot-pressed pure Si<sub>3</sub>N<sub>4</sub>, is slightly increased by Si<sub>2</sub>N<sub>2</sub>O phase. On the basis of these suggestions, Si<sub>2</sub>N<sub>2</sub>O phase influences the phase transformation rather than the densification of  $Si_3N_4$ ; the phase transformation of Si<sub>3</sub>N<sub>4</sub> is not always accompanied by densification [12]. Also, zirconia existing in this composite as a mono and cubic phase, was reported by Claussen as a "nitrogen stabilized zirconia" [10]. For this cubic phase, Lange also reported the  $ZrO_{2-2x}N_{4x/3}$   $0.25 \le x \le 0.43$  (zirconium oxynitride) in  $Si_3N_4$ -ZrO<sub>2</sub> composite [4].

The XRD pattern of Si<sub>3</sub>N<sub>4</sub> with 3Y ZrO<sub>2</sub> composite was composed of cubic or tetragonal  $ZrO_2$ ,  $\beta$ -Si<sub>3</sub>N<sub>4</sub> and Si<sub>2</sub>N<sub>2</sub>O peaks (Fig. 4d); the XRD patterns of Si<sub>3</sub>N<sub>4</sub> with 6Y and 8Y ZrO<sub>2</sub> composite were similar to those of Si<sub>3</sub>N<sub>4</sub> with 3Y ZrO<sub>2</sub> composite. As described earlier, if  $Y_2O_3$  in zyttrite mainly acted as a sintering aid rather than a stabilizer for zirconia, it might be expected that yttria-stabilized cubic zirconia would be transformed to tetragonal phase which had a lower  $Y_2O_3$  content [13]. From TEM works, the presence of the tetragonal ZrO<sub>2</sub> in Si<sub>3</sub>N<sub>4</sub> with 8Y ZrO<sub>2</sub> composite was confirmed as shown in Fig. 5. This result indicates that the zirconia which is stable in the cubic region is moved to the low Y2O3 content region, i.e. tetragonal + cubic region, by diffusion of  $Y_2O_3$  from zyttrite during hot-pressing.

### 3.2. $Si_3N_4$ –ZrO<sub>2</sub> reaction couples

### 3.2.1. Microstructures of reaction couples

To investigate the reaction product of  $Si_3N_4$ -ZrO<sub>2</sub>, reaction couples were used. Fig. 6 shows optical micrographs of the interfaces between  $Si_3N_4$  and 0Y, 3Y, and 8Y zirconia. In the  $Si_3N_4$ -OY ZrO<sub>2</sub> reaction

\* $\beta$  fraction was determined by comparing the intensities of  $\alpha(210)$  and  $\beta(210)$  diffraction peaks, in a manner described by Gazzara and Messier [11]. In this case,  $\beta$  fraction was 0.203.



Figure 5 Transmission electron micrographs of hot-pressed Si<sub>3</sub>N<sub>4</sub> with 30 vol % 8 mol % Y<sub>2</sub>O<sub>3</sub>-doped zirconia: (a) bright-field image and (b) selected-area diffraction pattern of Z region in (a);  $B = [0\,1\,1]c$ , t (S, Si<sub>3</sub>N<sub>4</sub>; Z, ZrO<sub>2</sub>).

couple, no significant reaction layer could be shown and the interface is flat (Fig. 6a). Recently, in the  $\alpha/\beta$ phase transformation of  $Si_3N_4$ ,  $\beta$ -Si<sub>3</sub>N<sub>4</sub> phase was precipitated via silicon melts [12, 14, 15]. A similar change in morphology was observed in the reaction layer between  $Si_3N_4$  and zyttrite. Both interfaces of the  $Si_3N_4$ -3Y and 8Y ZrO<sub>2</sub> reaction couples are rough, and a bright reaction layer containing a large precipitated phase can be seen (Fig. 6b, c). At the interface between  $Si_3N_4$ and the bright reaction layer (marked by arrows), a fine precipitated phase is observed. The interface between  $ZrO_2$  and the bright reaction layer was easily separated because of their large thermal expansion mismatch  $(\text{Si}_3\text{N}_4: \simeq 3.5 \times 10^{-6}, \text{ZrO}_2: \simeq 8 \text{ to } 10 \times 10^{-6} \text{ C}^{-1}).$ Scanning electron micrographs of Si<sub>3</sub>N<sub>4</sub>-3Y ZrO<sub>2</sub> reaction couple show glassy phase (Fig. 7a) and elongated  $\beta$ -Si<sub>3</sub>N<sub>4</sub> (Fig. 7b) at the reaction layer; these





micrographs were obtained from the viewing angle which was vertical to the reaction layer and parallel to the hot-pressing direction. However, the central part of Si<sub>3</sub>N<sub>4</sub> in the reaction couple contains equi-axed  $\beta$ -Si<sub>3</sub>N<sub>4</sub> of initial morphology (Fig. 7c), and spherical zirconia grains (2 to 6  $\mu$ m) (Fig. 7d) exist in the outer part of the reaction layer. On the basis of observation of the above microstructure, it is considered that Y<sub>2</sub>O<sub>3</sub> diffuses from the zyttrite reacts with Si<sub>3</sub>N<sub>4</sub> during hotpressing and forms a glass phase. Accompanying this, the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> can occur via this phase.

#### 3.2.2 Reaction products of Si<sub>3</sub>N<sub>4</sub>-ZrO<sub>2</sub> reaction couples

 $\alpha,\beta$ -Si<sub>3</sub>N<sub>4</sub> and strong Si<sub>2</sub>N<sub>2</sub>O peaks could be detected in the Si<sub>3</sub>N<sub>4</sub>-0Y ZrO<sub>2</sub> reaction couple (Fig. 8a). This result provides strong evidence for the formation of Si<sub>2</sub>N<sub>2</sub>O phase resulting from the reaction between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub>. Gauckler *et al.* [16] reported that the Si<sub>2</sub>N<sub>2</sub>O phase could be related to the reaction between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub>, and Terao [9] reported that the Si<sub>2</sub>N<sub>2</sub>O phase increased with the amount of added ZrO<sub>2</sub> in hot isostatically pressed-Si<sub>3</sub>N<sub>4</sub>. In the previous section,  $\beta$ -Si<sub>3</sub>N<sub>4</sub> and Si<sub>2</sub>N<sub>2</sub>O peaks were detected together in hot-pressed Si<sub>3</sub>N<sub>4</sub> with 0Y ZrO<sub>2</sub> composite. If cubic zirconia in Si<sub>3</sub>N<sub>4</sub> is present in the

*Figure 6* Optical micrographs of the interface of Si<sub>3</sub>N<sub>4</sub> and (a) pure zirconia, (b)  $3 \mod \% Y_2O_3$ -doped zirconia, (c)  $8 \mod \% Y_2O_3$ -doped zirconia reaction couple (S, Si<sub>3</sub>N<sub>4</sub>; Z, ZrO<sub>2</sub>, bright phase in (b), (c), reaction layer).





Figure 7 Scanning electron micrographs of  $Si_3N_4$  and  $3 \mod \% Y_2O_3$ -doped zirconia reaction couple: (a) and (b) at interface region, (c) at central part of  $Si_3N_4$  and (d) at zirconia region.

form of zirconium oxynitride [4, 10], therefore, the formation of silicon oxynitride can be considered as follows

$$ASi_3N_4 + BZrO_2 \rightarrow CZrO_{2-2x}N_{3x/4} + DSi_2N_2O$$

where A, B, C, D are constant. Oxygen atoms in  $ZrO_2$ are substituted by nitrogen atoms, and can form a silicon oxynitride phase. Subsequently,  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> occurs via Si<sub>2</sub>N<sub>2</sub>O glass during hot-pressing. Here, although the possibility of



Figure 8 XRD pattern of the interface of Si<sub>3</sub>N<sub>4</sub> and (a) pure zirconia, (b)  $3 \mod \% Y_2O_3$ -doped zirconia reaction couple: (A)  $\alpha$ -Si<sub>3</sub>N<sub>4</sub>, (B)  $\beta$ -Si<sub>3</sub>N<sub>4</sub>, (O) Si<sub>2</sub>N<sub>2</sub>O, (Z) cubic or tetragonal zirconia, (Y)  $Y_2Si_2O_7$ , (Y')  $YY_2Si_3N_4O_3$  peaks.

the reaction of  $Si_3N_4$  and surface silica to form a silicon oxynitride is not ruled-out, it seems that this reaction does not actively occur in this system; if  $Si_2N_2O$  phase was actively formed by this reaction, a significant phase transformation would occur in the hot-pressed pure  $Si_3N_4$ .

In the case of the  $Si_3N_4$ -zyttrite reaction couple,  $\beta$ -Si<sub>3</sub>N<sub>4</sub>, Si<sub>2</sub>N<sub>2</sub>O, Y<sub>2</sub>Si<sub>3</sub>N<sub>4</sub>O<sub>3</sub> (silicon yttrium oxynitride), and  $Y_2Si_2O_7$  (yttrialite) peaks were detected (Fig. 8b). For the Y<sub>2</sub>Si<sub>2</sub>O<sub>7</sub> phase, Clark [17] reported that the  $\alpha/\beta$  phase transformation and the densification of Si<sub>3</sub>N<sub>4</sub> could occur via the Y<sub>2</sub>Si<sub>2</sub>O<sub>7</sub> phase. Also, the  $Y_2Si_3N_4O_3$  phase was frequently observed in  $Si_3N_4$ sintered with Y<sub>2</sub>O<sub>3</sub> [18-20]. Therefore, in this system, the phase transformation can take place via  $Si_2N_2O_1$ ,  $Y_2Si_3N_4O_3$ , and  $Y_2Si_2O_7$  phases. However, it is not possible to determine the phase which affects the phase transformation dominantly rather than the others. It is suggested that the major reaction products of the reaction between Si<sub>3</sub>N<sub>4</sub> and zyttrite are  $Y_2Si_3N_4O_3$  and  $Y_2Si_2O_7$  phase, which can play an important role in the densification of Si<sub>3</sub>N<sub>4</sub>-zyttrite composites.

#### Conclusions

1. The role of pure  $ZrO_2$  on densification was not effective in obtaining full density of  $Si_3N_4$ - $ZrO_2$  composite, but most  $\alpha$ - $Si_3N_4$  phase was transformed to  $\beta$ - $Si_3N_4$ , resulting from the formation of  $Si_2N_2O$  phase.

2. In Si<sub>3</sub>N<sub>4</sub>-zyttrite composite, nearly full density (>97%) could be obtained by the addition of 5 vol % 6Y or 8Y ZrO<sub>2</sub>, but the densification did not occur sufficiently in the case of the addition of 3Y ZrO<sub>2</sub>. From these results, it is suggested that Y<sub>2</sub>O<sub>3</sub> diffused from the added zyttrite promotes the densification of the Si<sub>3</sub>N<sub>4</sub>-zyttrite composite, and the densification depends on the content of Y<sub>2</sub>O<sub>3</sub> in the zyttrite. Related to this, a tetragonal zirconia phase stable in the cubic + tetragonal region was observed.

3. In the Si<sub>3</sub>N<sub>4</sub>-pure ZrO<sub>2</sub> reaction couple, the reaction between Si<sub>3</sub>N<sub>4</sub> and ZrO<sub>2</sub> resulted in the formation of Si<sub>2</sub>N<sub>2</sub>O phase, and the  $\alpha/\beta$  phase transformation of Si<sub>3</sub>N<sub>4</sub> occurred via this Si<sub>2</sub>N<sub>2</sub>O phase. In the Si<sub>3</sub>N<sub>4</sub>zyttrite reaction couple, a bright reaction layer containing large and fine  $\beta$ -Si<sub>3</sub>N<sub>4</sub> precipitates was observed. From the XRD analysis of this reaction layer, it is suggested that the reaction products of the reaction between Si<sub>3</sub>N<sub>4</sub> and zyttrite, Y<sub>2</sub>Si<sub>3</sub>N<sub>4</sub>O<sub>3</sub> and Y<sub>2</sub>Si<sub>2</sub>O<sub>7</sub> phases, play an important role in the densification of Si<sub>3</sub>N<sub>4</sub>-zyttrite composite.

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